## Att. Docket No. 10191/1629

Appl. Serial No.

09/720,761

Confirmation No. 5642

Title

METHOD OF PLASMA

INITED STATES PATENT AND TRADEMARK OFFICE

**ETCHING OF SILICON** 

Applicant(s)

Franz LAERMER et al.

Filed

March 26, 2001

TC/A.U.

1765

:

Examiner

Kin Chan Chen

Docket No.

10191/1629

Customer No.

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(33,865)

## AMENDMENT AFTER A FINAL OFFICE ACTION

SIR:

In response to the Final Office Action mailed on June 7, 2004 (the three-month response date for which has been extended by two months from September 7, 2004 to November 7, 2004), please reconsider the above-identified application based on the following:

Amendments to the Claims are reflected in the listing of the claims which begins on page 2 of this paper.

Remarks begin on page 7 of this paper.